



**CHENMKO ENTERPRISE CO.,LTD**

**SURFACE MOUNT  
General Purpose Transistor**

**VOLTAGE 50 Volts CURRENT 0.15 Ampere**

**2SC2412TPT**

*Lead free devices*

**APPLICATION**

\* Small Signal Amplifier .

**FEATURE**

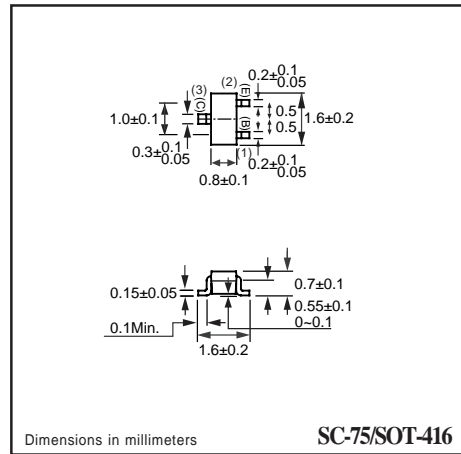
- \* Surface mount package. (SC-75/SOT-416)
- \* Low saturation voltage V
- \* Low cob. Cob=2.0pF(Typ); $f_{(sat)}=-0.4V(max.)$ (Ic=50mA)
- \* Pc= 200mW (mounted on ceramic substrate).
- \* High saturation current capability.

**CONSTRUCTION**

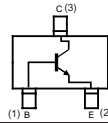
- \* NPN Silicon Transistor
- \* Epitaxial planner type

**MARKING**

- \* HFE (Q):QA
- \* HFE (R):RA
- \* HFE (S):SA



**CIRCUIT**



**MAXIMUM RATINGS** ( At TA = 25°C unless otherwise noted )

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage	Open Emitter	V <sub>CB0</sub>	-	60	Volts
Collector - Emitter Voltage	Open Base	V <sub>CE0</sub>	-	50	Volts
Emitter - Base Voltage	Open Collector	V <sub>EB0</sub>	-	7	Volts
Collector Current DC		I <sub>c</sub>	-	150	mAmps
Peak Collector Current		I <sub>CM</sub>	-	150	mAmps
Peak Base Current		I <sub>BM</sub>	-	15	mAmps
Total Power Dissipation	T <sub>A</sub> ≤ 25°C; Note 1	P <sub>TOT</sub>	-	200	mW
Storage Temperature		T <sub>STG</sub>	-55	+150	°C
Junction Temperature		T <sub>J</sub>	-	+150	°C
Operating Ambient Temperature		T <sub>AMB</sub>	-55	+150	°C

**Note**

1. Transistor mounted on ceramic substrate 50mmX50mmX0.8t.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

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## RATING CHARACTERISTICS ( 2SC2412TPT )

**ELECTRICAL CHARACTERISTICS** ( At  $T_A = 25^\circ\text{C}$  unless otherwise noted )

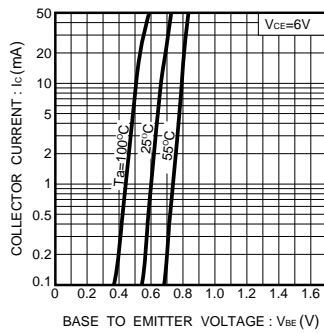
PARAMETERS	CONDITION	SYMBOL	MIN.	TYPE	MAX.	UNITS
Collector Cut-off Current	$I_E=0; V_{CB}=60\text{V}$	$I_{CBO}$	-	-	0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_C=0; V_{EB}=7\text{V}$	$I_{CEO}$	-	-	0.1	$\mu\text{A}$
DC Current Gain	$V_{CE}=6\text{V};$ Note 1 $I_C=1\text{mA};$ Note 2	$h_{FE}$	120	-	560	
Collector-Emitter Saturation Voltage	$I_C=50\text{mA}; I_B=5\text{mA}$	$V_{CEsat}$	-	-	0.4	Volts
Base-Emitter Saturatio Voltage	$I_C=50\text{mA}; I_B=5\text{mA}$	$V_{BEsat}$	-	-	1.1	mVolts
Output Collector Capacitance	$I_E=i_E=0; V_{CB}=12\text{V};$ $f=1\text{MHz}$	$C_{ob}$	-	2	3.5	pF
Transition Frequency	$I_C=2\text{mA}; V_{CE}=12\text{V};$ $f=100\text{MHz}$	$f_T$	-	180	-	MHz

**Note :**

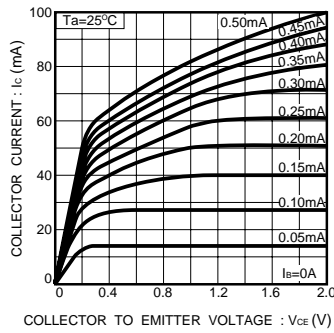
1. Pulse test:  $t_p \leq 300\mu\text{Sec}; \delta \leq 0.02$ .
2.  $h_{FE}$ : Classification Q: 120 to 270, R: 180 to 390, S: 270 to 560

## RATING CHARACTERISTIC CURVES ( 2SC2412TPT )

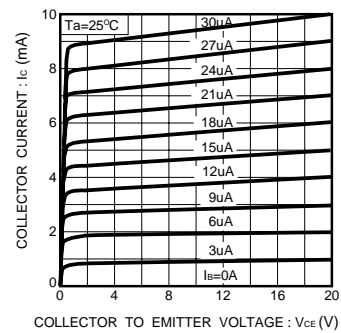
**Fig.1** Grounded emitter propagation characteristics



**Fig.2** Grounded emitter output characteristics (1)



**Fig.3** Grounded emitter output characteristics (2)



## RATING CHARACTERISTIC CURVES ( 2SC2412TPT )

Fig.4 DC current gain vs. collector current (1)

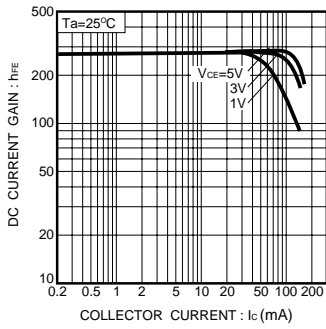


Fig.5 DC current gain vs. collector current (2)

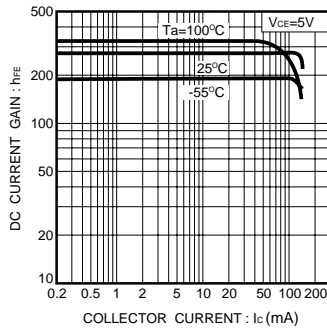


Fig. 6 Collector-emitter saturation voltage vs. collector current

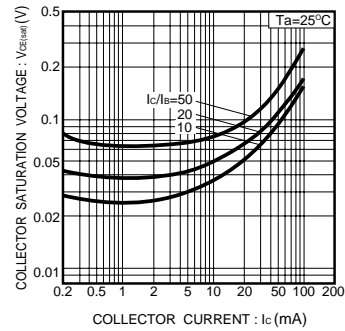


Fig.7 Collector-emitter saturation voltage vs. collector current (1)

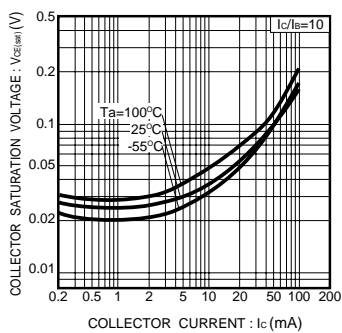


Fig.8 Collector-emitter saturation voltage vs. collector current (2)

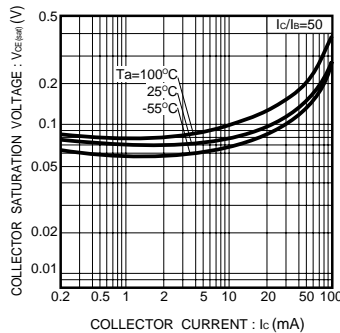


Fig.9 Gain bandwidth product vs. emitter current

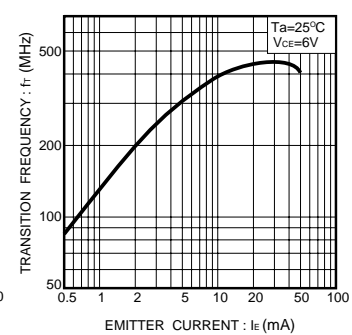


Fig.10 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

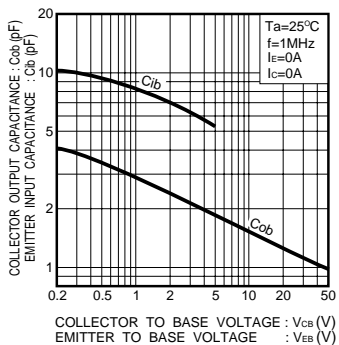


Fig.11 Base-collector time constant vs. emitter current

